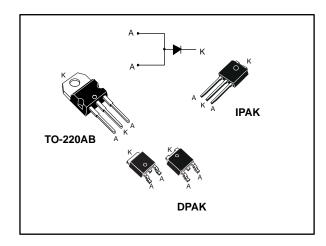


## **FERD20S100S**

### 100 V field-effect rectifier diode

Datasheet - production data



### **Features**

- ST advanced rectifier process
- Stable leakage current over reverse voltage
- Reduced leakage current
- Low forward voltage drop
- High frequency operation
- ECOPACK®2 compliant component

### **Description**

The device is based on a proprietary technology that achieves the best in class  $V_F/I_R$  trade-off for a given silicon surface. This 100 V rectifier has been optimized for use in confined casing applications where both efficiency and thermal performance matter. With a lower dependency of leakage current ( $I_R$ ) and forward voltage ( $V_F$ ) in function of temperature, the thermal runaway risk is reduced. Therefore, it can advantageously replace 100 V Schottky diodes.

**Table 1: Device summary** 

Symbol	Value
I <sub>F(AV)</sub>	20 A
$V_{RRM}$	100 V
V <sub>F</sub> (max.)	0.415 V
I <sub>R</sub> (max.)	110 μΑ
T <sub>j</sub> (max.)	175 °C

This is information on a product in full production.

Characteristics FERD20S100S

### 1 Characteristics

Table 2: Absolute ratings (limiting values at 25 °C, unless otherwise specified, anode terminals short-circuited)

Symbol	Parameter			Value	Unit
V <sub>RRM</sub>	Repetitive peak reverse voltage			100	V
I <sub>F(RMS)</sub>	Forward rms current	Forward rms current			
I <sub>F(AV)</sub>	Average forward current $\delta$ = 0.5, square wave $T_C$ = 150 °C		20	Α	
	$I_{FSM}$ Surge non repetitive forward $t_p = 10 \text{ ms}$ sinusoidal		TO-220AB	220	Α
IFSM			DPAK, IPAK	150	Α
T <sub>stg</sub>	Storage temperature range			-65 to +175	°C
Tj	Maximum operating junction temperature (1)			175	°C

#### Notes:

**Table 3: Thermal resistance parameters** 

Symbol	Parameter	Value	Unit
R <sub>th(j-c)</sub>	Junction to case	1.3	°C/W

Table 4: Static electrical characteristics (anode terminals short circuited)

Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
		T <sub>j</sub> = 25 °C	\/- \/	-		110	μΑ
I <sub>R</sub> <sup>(1)</sup>	Reverse leakage current	T <sub>j</sub> = 125 °C	$V_R = V_{RRM}$	-	6	12	A
		T <sub>j</sub> = 125 °C	V <sub>R</sub> = 70 V	-	3	6	mA
		T <sub>j</sub> = 25 °C	I_ 2 A	-	0.395	0.445	
		T <sub>j</sub> = 125 °C	I <sub>F</sub> = 2 A	-	0.36	0.415	
		T <sub>j</sub> = 25 °C	I <sub>F</sub> = 5 A	-	0.520	0.585	
V <sub>F</sub> <sup>(2)</sup>	Forward voltage drop	T <sub>j</sub> = 125 °C		-	0.500	0.555	V
		T <sub>j</sub> = 25 °C	1 40 4	-	0.680	0.780	
		T <sub>j</sub> = 125 °C	I <sub>F</sub> = 10 A	-	0.600	0.660	
		T <sub>j</sub> = 125 °C	I <sub>F</sub> = 20 A	-	0.690	0.760	

### Notes:

 $^{(1)}$ Pulse test:  $t_p$  = 5 ms,  $\delta$  < 2%

 $^{(2)}$ Pulse test: tp = 380 µs,  $\delta$  < 2%

To evaluate the conduction losses use the following equation:

 $P = 0.45 \text{ x } I_{F(AV)} + 0.021 \text{ x } I_{F^2(RMS)}$ 

 $<sup>^{(1)}(</sup>dP_{tot}/dT_j) < (1/R_{th(j-a)}) \ condition \ to \ avoid \ thermal \ runaway \ for \ a \ diode \ on \ its \ own \ heatsink.$ 

FERD20S100S Characteristics

Tamb(°C)

150

 $V_R(V)$ 

175

125

## 1.1 Characteristics (curves)

15

10

1.E-02

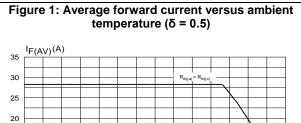
1.E-03

10

 $\delta = tp/T$ 

25

50



75

100

Figure 2: Relative variation of thermal impedance junction to case versus pulse duration 1.0 0.9 0.8 0.7 0.6 0.5 0.4 0.3 0.2 0.1 tp(s) 0.0 1.E-04 1.E-01 1.E-03 1.E-02

voltage applied (typical values)

1.E+02

IR(mA)

T<sub>1</sub>= 150 °C

T<sub>1</sub>= 125 °C

T<sub>1</sub>= 75 °C

1.E+01

T<sub>1</sub>= 50 °C

Figure 3: Reverse leakage current versus reverse

Figure 4: Junction capacitance versus reverse voltage applied (typical values)

C(pF)

10000

1000

1000

1000

1000

1000

1000

1000

Figure 5: Forward voltage drop versus forward current (typical values, log scale)

100.0

I<sub>F</sub>(A)

10.0

T<sub>1</sub>=75 ° C

T<sub>2</sub>=25 ° C

1.0

0.1

0.0

0.1

0.2

0.3

0.4

0.5

0.6

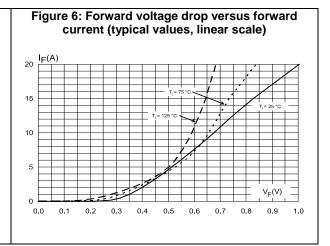
0.7

0.8

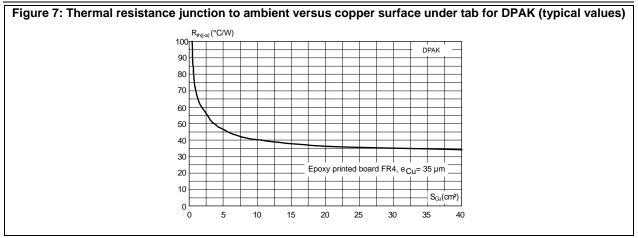
0.9

1.0

40 50 60 70 80 90 100



Characteristics FERD20S100S



FERD20S100S Package information

## 2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: **www.st.com**. ECOPACK® is an ST trademark.

- Cooling method: by conduction (C)
- Epoxy meets UL 94,V0
- Recommended torque value: 0.55 N·m (for TO-220AB)
- Maximum torque value: 0.6 N·m (for TO-220AB)

## 2.1 IPAK package information

Figure 8: IPAK package outline

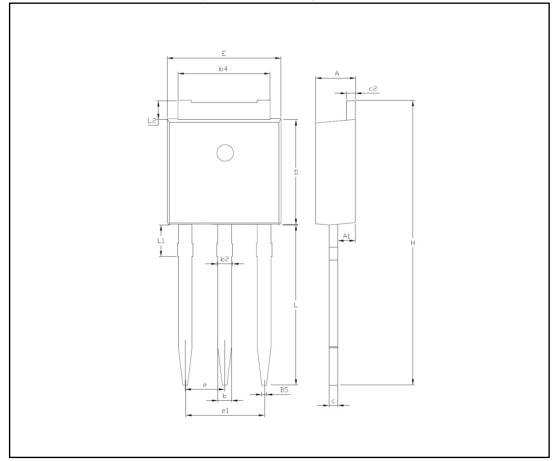




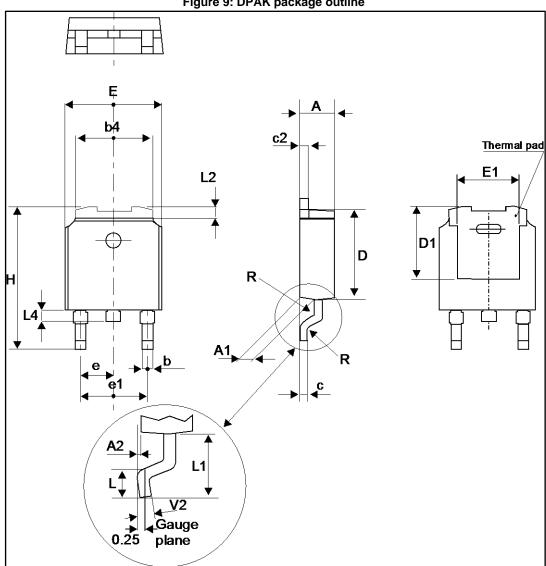
Table 5: IPAK package mechanical data

	Dimensions			
Ref.	Millim	eters	Inc	hes
	Min.	Max.	Min.	Max.
А	2.20	2.40	0.087	0.094
A1	0.90	1.10	0.035	0.043
b	0.64	0.90	0.025	0.035
b2		0.95		0.037
b4	5.20	5.43	0.205	0.214
B5	0.30	typ.	0.012 typ.	
С	0.45	0.60	0.018	0.024
c2	0.46	0.60	0.018	0.024
D	6.00	6.20	0.236	0.244
Е	6.40	6.65	0.252	0.261
е	2.28	typ.	typ.0	0.090
e1	4.40	4.60	0.173	0.181
Н	16.10 typ.		0.634	4 typ.
L	9.0	9.60	0.354	0.378
L1	0.80	1.20	0.031	0.047
L2	0.80 typ.	1.25	0.031 typ.	0.049
V1	+10°		+10	

FERD20S100S Package information

#### **DPAK** package information 2.2

Figure 9: DPAK package outline



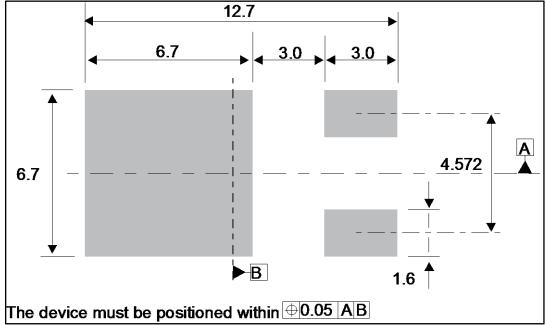


This package drawing may slightly differ from the physical package. However, all the specified dimensions are guaranteed.

Table 6: DPAK package mechanical data

	Dimensions				
Ref.	Mill	imeters	Inc	hes	
	Min.	Max.	Min.	Max.	
А	2.18	2.40	0.085	0.094	
A1	0.90	1.10	0.035	0.043	
A2	0.03	0.23	0.001	0.009	
b	0.64	0.90	0.025	0.035	
b4	4.95	5.46	0.194	0.215	
С	0.46	0.61	0.018	0.024	
c2	0.46	0.60	0.018	0.023	
D	5.97	6.22	0.235	0.244	
D1	4.95	5.60	0.194	0.220	
E	6.35	6.73	0.250	0.265	
E1	4.32	5.50	0.170	0.216	
е	2.2	86 typ.	0.09	0 typ.	
e1	4.40	4.70	0.173	0.185	
Н	9.35	10.40	0.368	0.409	
L	1.0	1.78	0.039	0.070	
L2		1.27		0.050	
L4	0.60	1.02	0.023	0.040	
V2	-8°	+8°	-8°	+8°	

Figure 10: DPAK recommended footprint (dimensions in mm)



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FERD20S100S Package information

# 2.3 TO-220AB package information

Figure 11: TO-220AB package outline

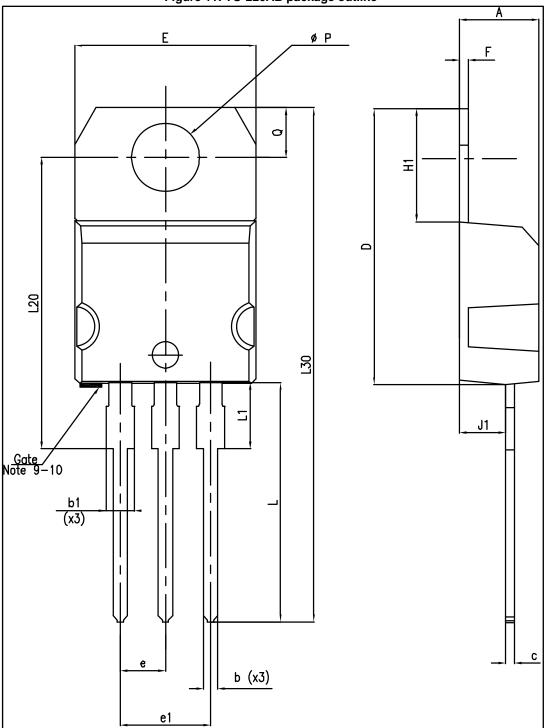


Table 7: TO-220AB package mechanical data

	Dimensions				
Ref.	Millim	neters	Inc	nches	
	Min.	Max.	Min.	Max.	
А	4.40	4.60	0.173	0.181	
b	0.61	0.88	0.024	0.035	
b1	1.14	1.70	0.045	0.067	
С	0.48	0.70	0.019	0.028	
D	15.25	15.75	0.600	0.620	
Е	10.00	10.40	0.394	0.409	
е	2.40	2.70	0.094	0.106	
e1	4.95	5.15	0.195	0.203	
F	0.51	0.60	0.020	0.024	
J1	2.40	2.72	0.094	0.107	
H1	6.20	6.60	0.244	0.256	
L	13.00	14.00	0.512	0.551	
L1	3.50	3.93	0.138	0.155	
L20	16.40 typ.		0.646 typ.		
L30	28.90 typ.		1.1	138	
Ø P	3.75	3.85	0.148	0.156	
Q	2.65	2.95	0.104	0.116	

FERD20S100S Ordering information

# 3 Ordering information

**Table 8: Ordering information** 

Order code	Marking	Package	Weight	Base qty.	Delivery mode
FERD20S100STS	FD20S100STS	TO-220AB	1.38 g	50	Tube
FERD20S100SB-TR	FD20 S100S	DPAK	0.35 g	2500	Tape and reel
FERD20S100SH	FD20 S100S	IPAK	0.32 g	75	Tube

# 4 Revision history

**Table 9: Document revision history** 

Date	Revision	Changes
03-Jun-2016	1	Initial release.
14-Nov-2017	2	Updated cover page.

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